

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

- 1-4. (Cancelled)
5. (New) A method to manufacture a semiconductor device, comprising:
preparing a semiconductor wafer including a plurality of semiconductor chip forming sections each having an electrode;
forming a first through hole in the electrode;
forming a second through hole penetrating the semiconductor wafer, the second through hole communicating with the first through hole; and
forming a conduction layer that extends via the first and second through holes from a first surface of each of the semiconductor chip forming sections on which the electrode is formed to a second surface opposite to the first surface, the conduction layer being electrically connected to the electrode.
6. (New) The method to manufacture a semiconductor device according to claim 5, the second through hole having a straight internal wall.
7. (New) The method to manufacture a semiconductor device according to claim 5, a first size of the first through hole being the same as a second size of the second through hole.
8. (New) The method to manufacture a semiconductor device according to claim 5, a first size of the first through hole being greater than a second size of the second through hole.
9. (New) The method to manufacture a semiconductor device according to claim 5, further comprising:

forming a dielectric film covering the electrode and an interior of the first through hole;

forming a third through hole penetrating the first dielectric film, the third through hole exposing the electrode,

the conduction layer being electrically connected to the electrode via the third through hole.

10. (New) The method to manufacture a semiconductor device according to claim 5, further comprising:

forming a second dielectric film on an internal wall surface of the second through hole, the conduction layer being formed on the second dielectric film.

11. (New) The method to manufacture a semiconductor device according to claim 5, including the steps of:

forming a first dielectric film covering the electrode and an interior of the first through hole;

forming a second dielectric film on an internal wall surface of the second through hole;

forming an opening penetrating the first and second dielectric film, the opening exposing the electrode, the conduction layer being electrically connected to the electrode via the opening.

12. (New) The method to manufacture a semiconductor device according to claim 5, the first through hole being formed by a dry etching.

13. (New) The method to manufacture a semiconductor device according to claim 5, the conduction layer being formed by the plating method.